Technical Data Sheet
5mm Infrared LED, T-1

IR383/H40/P3

Features

- High reliability
- 2.54mm lead spacing
- Low forward voltage
- Good spectral matching to Si photodetector

Descriptions

EVERLIGHT's infrared emitting diode (IR383/H40/P3) is a high intensity diode, molded in a blue transparent plastic package.
The device is spectrally matched with phototransistor, photodiode and infrared receiver module.

Applications

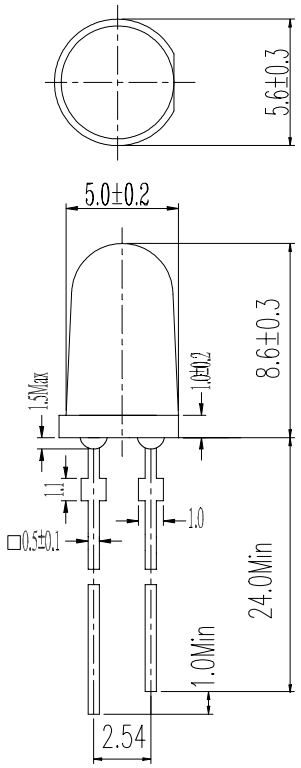
- Auto flush
- Optoelectronic switch
- Floppy disk drive
- Infrared applied system

Device Selection Guide

LED Part No.	Chip Material	Lens Color
IR	GaAlAs	Blue

Device No:DIR-038-213

Package Dimensions



Notes: 1.All dimensions are in millimeters
2.Tolerances unless dimensions ± 0.1mm

Absolute Maximum Ratings (Ta=25℃)

Parameter	Symbol	Rating	Units
Continuous Forward Current	I_F	100	mA
Peak Forward Current	I_{FP}	1.0	A
Reverse Voltage	V_R	5	V
Operating Temperature	T_{opr}	-40 ~ +85	℃
Storage Temperature	T_{stg}	-40 ~ +85	℃
Soldering Temperature	T_{sol}	260	℃
Power Dissipation at(or below) 25℃ Free Air Temperature	P_d	150	mW

Notes: *1:I_{FP} Conditions--Pulse Width≦100 μ s and Duty≦1%.
*2:Soldering time≦5 seconds.

Device No:DIR-038-213

Electro-Optical Characteristics (Ta=25℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Units
Radiant Intensity	E_e	I_F=20mA	4.0	8.9	--	mW/sr
		I_F=100mA Pulse Width≦100 μs and Duty≦1%	--	35	--	
		I_F=1A Pulse Width≦100 μs and Duty≦1%	--	450	--	
Peak Wavelength	λp	I_F=20mA	--	940	--	nm
Spectral Bandwidth	Δλ	I_F=20mA	--	45	--	nm
Forward Voltage	V_F	I_F=20mA	--	1.2	1.5	V
		I_F=100mA Pulse Width≦100 μs and Duty≦1%	--	1.4	1.8	
		I_F=1A Pulse Width≦100 μs and Duty≦1%	--	2.6	4.0	
Reverse Current	I_R	V_R=5V	--	--	10	μA
View Angle	2θ1/2	I_F=20mA	--	30	--	deg

Intensity Specifications for Bin Grading

Rank	Test Condition	Min	Max	Unit
K	I_F=20mA	4.0	6.4	mW/sr
L		5.6	8.9	
M		7.8	12.5	
N		11.0	17.6	

Device No:DIR-038-213

Typical Electro-Optical Characteristics Curves

Fig.1 Forward Current vs. Ambient Temperature

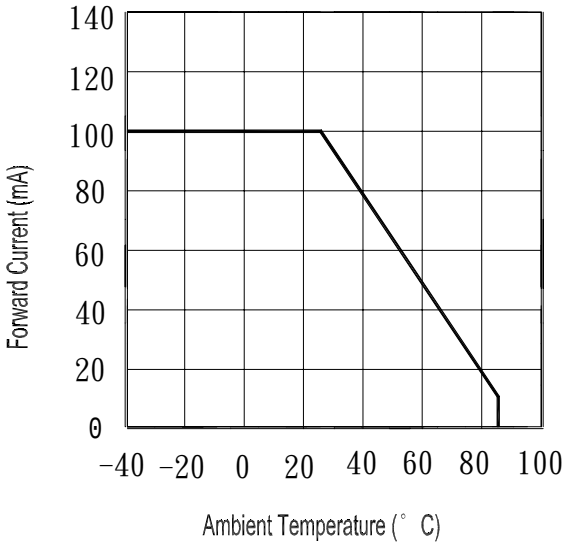


Fig.2 Spectral Distribution

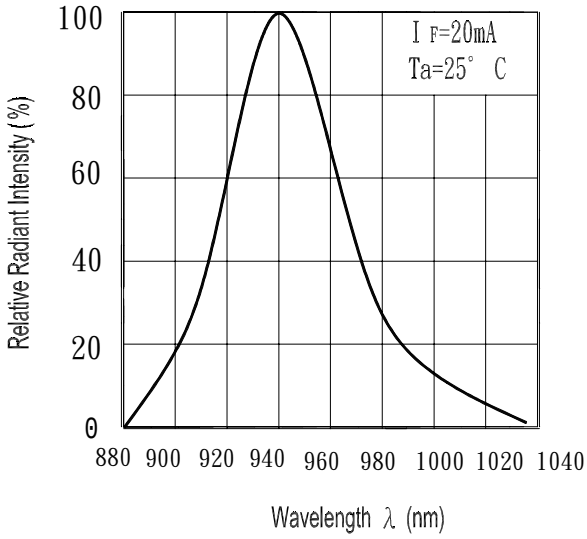


Fig.3 Peak Emission Wavelength vs. Ambient Temperature

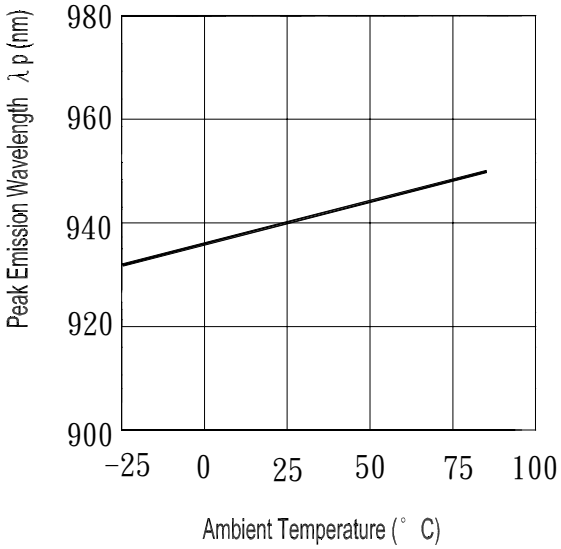
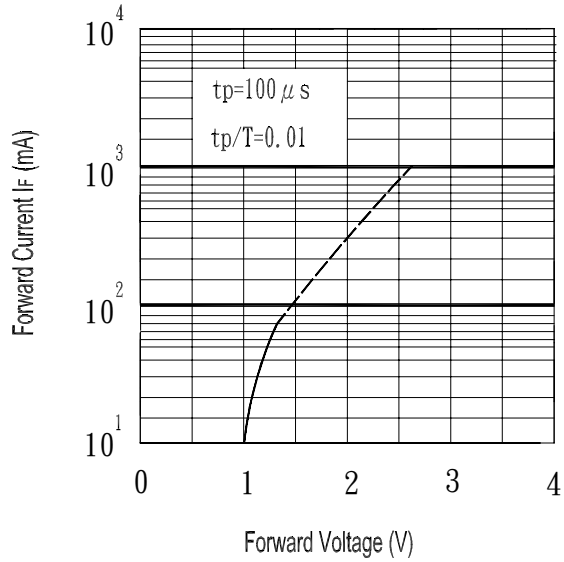


Fig.4 Forward Current vs. Forward Voltage



Device No:DIR-038-213

Typical Electro-Optical Characteristics Curves

Fig.5 Relative Intensity vs. Forward Current

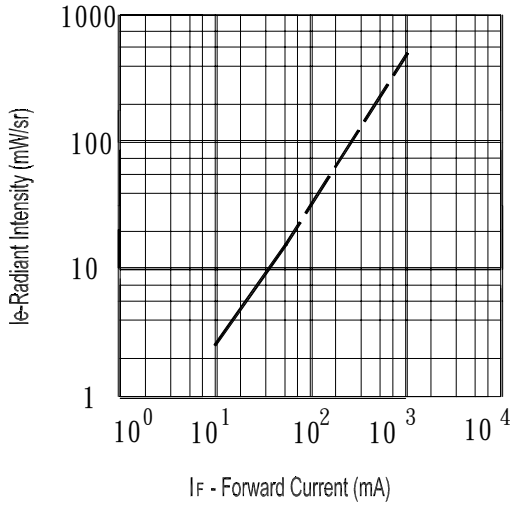


Fig.6 Relative Radiant Intensity vs. Angular Displacement

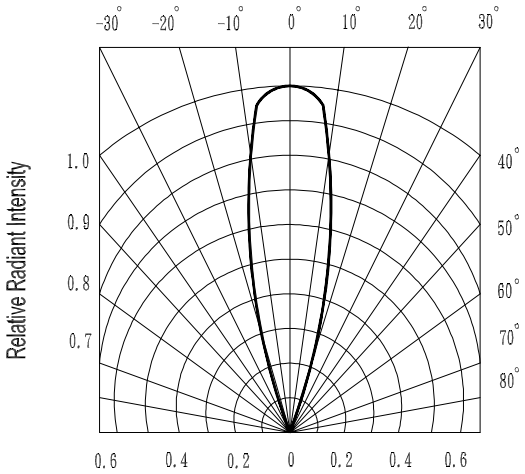


Fig.7 Relative Intensity vs. Ambient Temperature (° C)

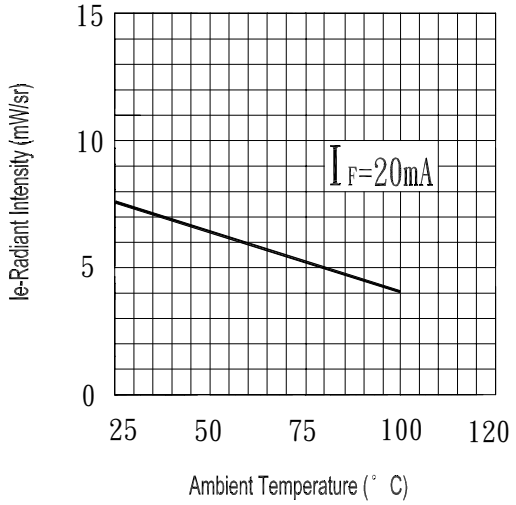
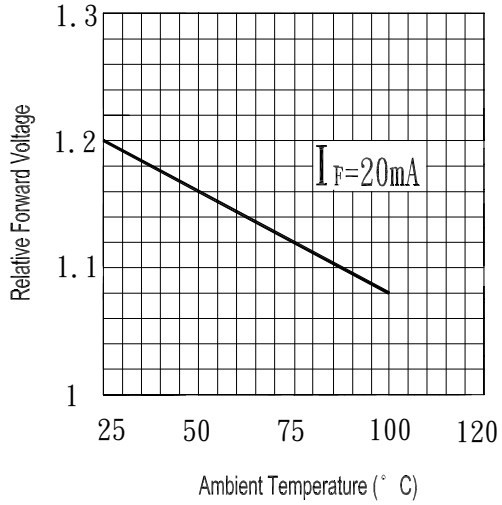


Fig.8 Forward Current vs. Ambient Temperature (° C)



Device No:DIR-038-213

Reliability Test Item And Condition

The reliability of products shall be satisfied with items listed below.

Confidence level：90%

LTPD：10%

NO.	Item	Test Conditions	Test Hours/ Cycles	Sample Sizes	Failure Judgement Criteria	Ac/Re
1	Solder Heat	TEMP.：260℃± 5℃	10secs	22pcs	$I_R \geqq U \times 2$ $Ee \leqq L \times 0.8$ $V_F \geqq U \times 1.2$ U：Upper Specification Limit L：Lower Specification Limit	0/1
2	Temperature Cycle	H：+85℃ 30mins ↕ 5mins L：-55℃ 30mins	50Cycle	22pcs		0/1
3	Thermal Shock	H：+100℃ 5mins ↕ 10secs L：-10℃ 5mins	50Cycle	22pcs		0/1
4	High Temperature Storage	TEMP.：+100℃	1000hrs	22pcs		0/1
5	Low Temperature Storage	TEMP.：-55℃	1000hrs	22pcs		0/1
6	DC Operating Life	I_F=20mA	1000hrs	22pcs		0/1
7	High Temperature/ High Humidity	85℃ / 85% R.H	1000hrs	22pcs		0/1

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Device No:DIR-038-213